

GaAs Semiconductor Laser Diode

Tunable Fabry-Perot Laser for External Cavity Operation



PRELIMINARY SPECIFICATION

RWE Laser

EYP-RWE-0980-08020-1500-SOT02-0000

General Product Information

| Application | Product |
|--------------|---|
| Spectroscopy | tunable 980 nm Fabry-Perot Laser |
| | for use in an External Cavity Diode Laser (ECDL) sealed SOT Housing |
| | Monitor Diode |
| | Monitor Diode |

Absolute Maximum Ratings

| | Symbol | Unit | min | typ | max |
|---------------------------------|----------------|------|-----|-----|-----|
| Storage Temperature | Ts | °C | -20 | | 85 |
| Operational Temperature at Case | T _C | °C | -20 | | 50 |
| Forward Current | I _F | mA | | | 120 |
| Reverse Voltage | V _R | V | | | 0 |
| Reverse voltage | V _R | V | | | |

Recommended Operational Conditions

| | Symbol | Unit | min | typ | max |
|---------------------------------|----------------|------|-----|-----|-----|
| Operational Temperature at case | T _C | °C | 15 | | 40 |
| Forward Current | I _F | mA | | | 100 |

Characteristics at T_{amb} 25 °C at Begin Of Life

| Symbol | Unit | min | typ | max |
|-----------------------|--|--|--|--|
| λ_{C} | nm | | 980 | |
| $\Delta\lambda_{tun}$ | nm | 900 | | 1000 |
| P _{opt} | mW | | 50 | |
| L | μm | | 1500 | |
| R _{ff} | | | 3 [.] 10 ⁻⁴ | 1 [.] 10 ⁻³ |
| | | | TE | |
| | λ _C Δλ _{tun} P _{opt} L | λ _c nm Δλ _{tun} nm P _{opt} mW L μm | λ _C nm Δλ _{tun} nm 900 P _{opt} mW L μm | $λ_c$ nm 980 $Δλ_{tun}$ nm 900 P_{opt} mW 50 L μm 1500 R_{ff} 3'10'4 |



Stress in excess of the Absolute Maximum Ratings can cause permanent damage to the device. Operation at the Absolute Maximum Rating for extended periods of time can adversely affect the device realibility and may lead to reduced operational life.

Measurement Conditions / Comments

Tuning range and output power are estimated from the gain profile of the laser. The actual achieved wavelength and power are strongly influenced by the external cavity. Therefore eagleyard Photonics will give no guarantee on these parameters.

Polarization parallel to Pin 2 - Pin 3 -plane

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 $U_{R MD}$

V

3

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PRELIMINARY SPECIFICATION

Reverse Voltage Monitor Diode

RWE Laser

typ

max

10

5

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Monitor Diode Parameter Symbol Unit min Monitor Detector Responsivity I_{mon} / P_{optic} µA / mW 1

Measurement Conditions / Comments

 $U_{R\,MD}=5$ V, $P_{opt\,ic}$: intracavity power of the ECDL



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reference plane: top side of TO header

PRELIMINARY SPECIFICATION

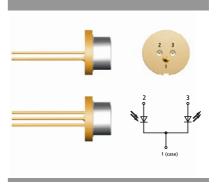
RWE Laser

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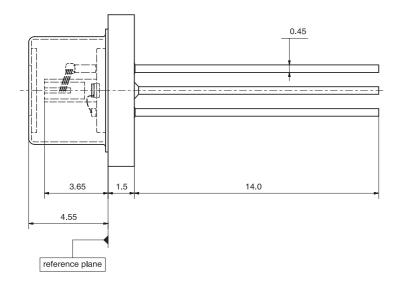
Package Dimensions

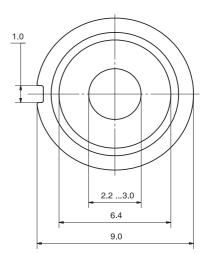
| | Symbol | Unit | min | typ | max |
|------------------|-----------------|------|------|------|------|
| Emission Plane | d _{EP} | mm | 3.50 | 3.65 | 3.70 |
| Housing Diameter | d | mm | | 9.0 | |
| Pin Length | I | mm | | 14.0 | |
| | | | | | |

| Package Pinout | М-Туре | |
|-----------------|--------|--|
| | | |
| Ground | 1 | |
| Photo Diode (+) | 2 | |
| Laser (+) | 3 | |



Package Drawings





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GaAs Semiconductor Las<u>er Diode</u>

Tunable Fabry-Perot Laser for External Cavity Operation



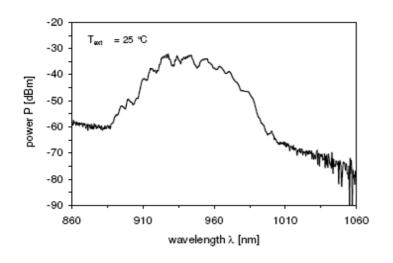
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Typical Measurement Results

Emission Spectrum measured without external feedback



Performance figures, data and any illustrative material provided in this specification are typical and must be specifically confirmed in writing by eagleyard Photonics before they become applicable to any particular order or contract. In accordance with the eagleyard Photonics policy of continuous improvement specifications may change without notice.

Unpacking, Installation and Laser Safety

Unpacking the laser diodes should only be done at electrostatic safe workstations (EPA). Though protection against electro static discharge (ESD) is implemented in the laser package, charges may occur at surfaces. Please store this product in its original package at a dry, clean place until final use. During device installation, ESD protection has to be maintained.

The RWE diode type is known to be sensitive against thermal stress. It should not be operated without appropriate optical feedback from an external cavity. Operating at moderate temperatures on propper heat sinks will contribute to a long lifetime of the diode.

The laser emission from this diode is close to the invisible infrared region of the electromagnetic spectrum. Avoid direct and/or indirect exposure to the free running beam. Collimating the free running beam with optics as common in optical instruments will increase thread to the human eye.

Each laser diode will come with an individual test protocol verifying the parameters given in this document.





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